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May 2014



FDA70N20

N-Channel UniFET™ MOSFET

200 V, 70 A, 35 mΩ

Features

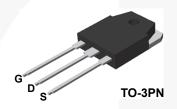
- $R_{DS(on)}$ = 35 m Ω (Max.) @ V_{GS} = 10 V, I_D = 35 A
- Low Gate Charge (Typ. 66 nC)
- · Low Crss (Typ. 89 pF)
- 100% Avalanche Tested

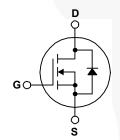
Applications

- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDA70N20	Unit	
V_{DSS}	Drain-Source Voltage		200	V	
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)		70 45	A A	
I _{DM}	Drain Current - Pulsed	(Note 1)	280	Α	
V _{GSS}	Gate-Source voltage		±30	V	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		1742	mJ	
I _{AR}	Avalanche Current	(Note 1)	70	Α	
E _{AR}	Repetitive Avalanche Energy (Note 1)		41.7	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns	
P _D	Power Dissipation (T _C = 25°C) - Derate Above 25°C		417 3.3	W W/°C	
$T_{J,}T_{STG}$	Operating and Storage Temperature Range		-55 to +150	°C	
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	FDA70N20	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.3	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDA70N20	FDA70N20	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics			ı		
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	200			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C		0.2		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 200V, V _{GS} = 0V V _{DS} = 160V, T _C = 125°C	1 1		1 10	μ Α μ Α
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 35A		0.029	0.035	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40V, I _D = 35A		47		S
Dynamic C	haracteristics			I .		
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V,	\	3050	3970	pF
C _{oss}	Output Capacitance	f = 1.0 MHz	-	750	980	pF
C _{rss}	Reverse Transfer Capacitance		-	89	130	pF
Switching	Characteristics				_	
t _{d(on)}	Turn-On Delay Time	V _{DD} = 100V, I _D = 70A		71	150	ns
t _r	Turn-On Rise Time	$R_G = 25\Omega$		235	480	ns
t _{d(off)}	Turn-Off Delay Time			65	140	ns
t _f	Turn-Off Fall Time	(Note 4)		39	88	ns
Qg	Total Gate Charge	V _{DS} = 160V, I _D = 70A		66	86	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10V	/	19		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		26		nC
Drain-Sour	ce Diode Characteristics and Maximur	n Ratings	/		9	•
I _S	Maximum Continuous Drain-Source Diode Forward Current				70	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F	orward Current			280	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 70A	-		1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 70A	-	175		ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt =100A/μs	-	4.1		μС

NOTES

^{1.} Repetitive rating: pulse-width limited by maximum junction temperature.

^{2.} L = 0.533 mH, I_{AS} = 70 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.

 $^{3.}I_{SD} \leq 70$ A, di/dt ≤ 200 A/µs, $V_{DD} \leq BV_{DSS}$, starting T_J = 25°C.

^{4.} Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

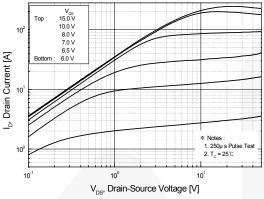


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

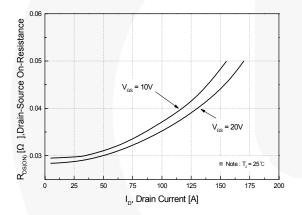


Figure 2. Transfer Characteristics

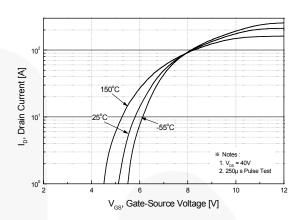


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

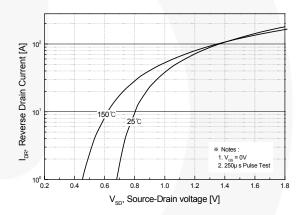


Figure 5. Capacitance Characteristics

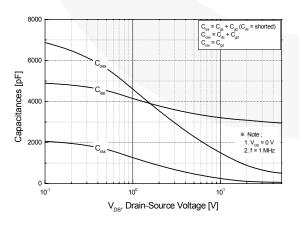
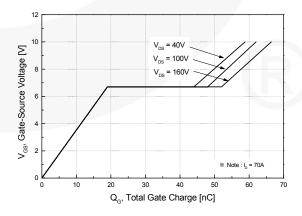


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

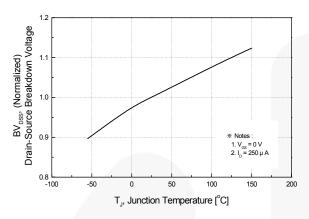


Figure 8. On-Resistance Variation vs. Temperature

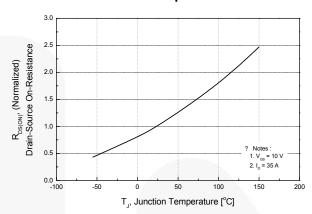


Figure 9. Safe Operating Area

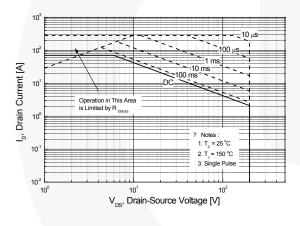


Figure 10. Maximum Drain Current vs. Case Temperature

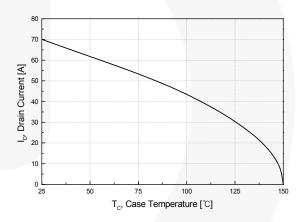
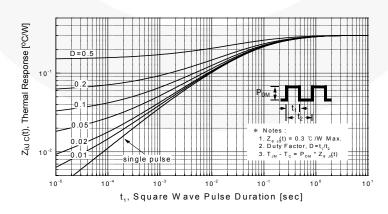


Figure 11. Transient Thermal Response Curve



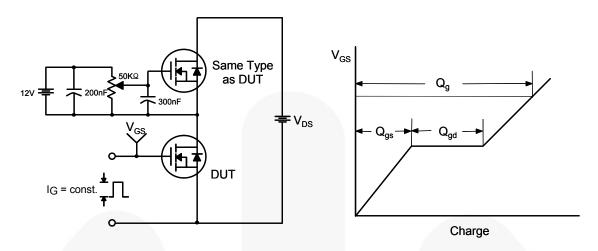


Figure 12. Gate Charge Test Circuit & Waveform

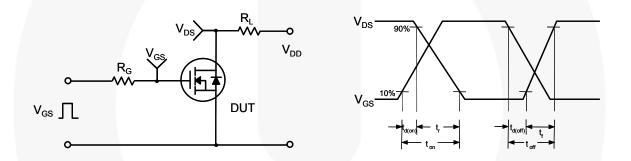


Figure 13. Resistive Switching Test Circuit & Waveforms

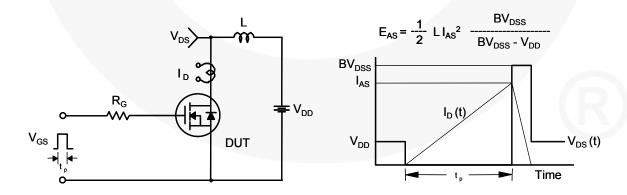


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

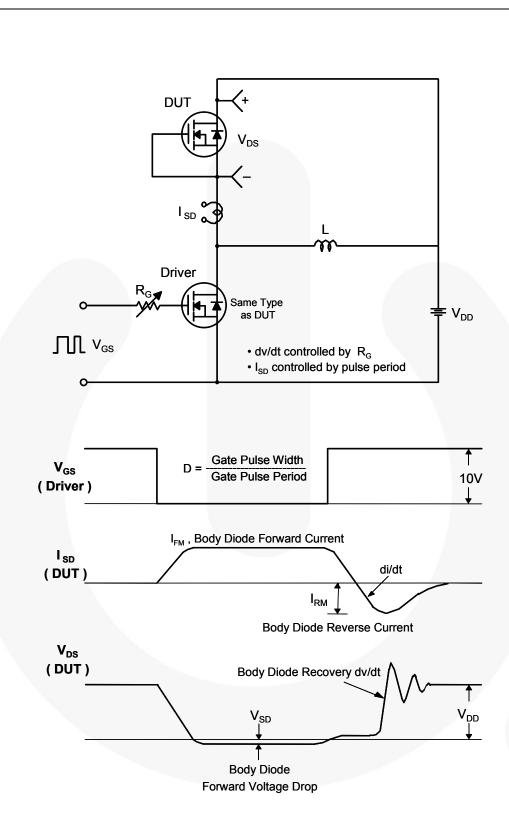
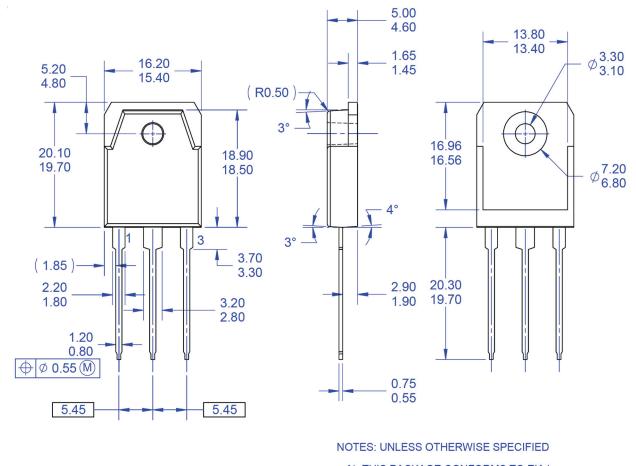
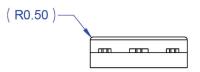


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
 E) DRAWING FILE NAME: TO3PN03AREV1.
- FAIRCHILD SEMICONDUCTOR.

Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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